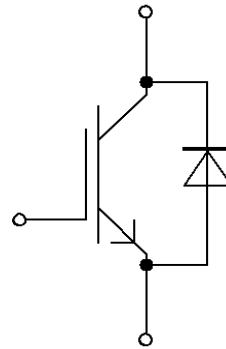


62mm C-Series 模块 采用第四代沟槽栅/场终止IGBT4和第四代发射极控制二极管
 62mm C-Series module with Trench/Fieldstop IGBT4 and Emitter Controlled 4 diode



$V_{CES} = 1200V$
 $I_{C\ nom} = 900A / I_{CRM} = 1800A$

典型应用

- 大功率变流器
- 电机传动
- UPS系统
- 风力发电机

Typical Applications

- High power converters
- Motor drives
- UPS systems
- Wind turbines

电气特性

- 提高工作结温 $T_{vj\ op}$
- 低 V_{CEsat}
- 无与伦比的坚固性
- V_{CEsat} 带正温度系数

Electrical Features

- Extended operating temperature $T_{vj\ op}$
- Low V_{CEsat}
- Unbeatable robustness
- V_{CEsat} with positive temperature coefficient

机械特性

- 4 kV 交流 1分钟 绝缘
- 封装的 CTI > 400
- 高爬电距离和电气间隙
- 高功率密度
- 绝缘的基板
- 标准封装

Mechanical Features

- 4 kV AC 1min insulation
- Package with CTI > 400
- High creepage and clearance distances
- High power density
- Isolated base plate
- Standard housing

Module Label Code

Barcode Code 128



DMX - Code



Content of the Code

Content of the Code	Digit
Module Serial Number	1 - 5
Module Material Number	6 - 11
Production Order Number	12 - 19
Datecode (Production Year)	20 - 21
Datecode (Production Week)	22 - 23

IGBT, 逆变器 / IGBT, Inverter

最大额定值 / Maximum Rated Values

集电极 - 发射极电压 Collector-emitter voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{CES}	1200	V
连续集电极直流电流 Continuous DC collector current	$T_C = 95^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$	$I_{C\text{nom}}$	900	A
集电极重复峰值电流 Repetitive peak collector current	$t_P = 1\text{ ms}$	I_{CRM}	1800	A
栅极 - 发射极峰值电压 Gate-emitter peak voltage		V_{GES}	+/-20	V

特征值 / Characteristic Values

			min.	typ.	max.		
集电极 - 发射极饱和电压 Collector-emitter saturation voltage	$I_C = 900\text{ A}, V_{GE} = 15\text{ V}$ $I_C = 900\text{ A}, V_{GE} = 15\text{ V}$ $I_C = 900\text{ A}, V_{GE} = 15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$V_{CE\text{sat}}$	1,70 2,00 2,10	2,05	V V V	
栅极阈值电压 Gate threshold voltage	$I_C = 32,0\text{ mA}, V_{CE} = V_{GE}, T_{vj} = 25^{\circ}\text{C}$		V_{GEth}	5,20	5,80	6,40	V
栅极电荷 Gate charge	$V_{GE} = -15\text{ V} \dots +15\text{ V}$		Q_G	7,40			μC
内部栅极电阻 Internal gate resistor	$T_{vj} = 25^{\circ}\text{C}$		R_{Gint}	0,9			Ω
输入电容 Input capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{ies}	56,0			nF
反向传输电容 Reverse transfer capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{res}	2,20			nF
集电极-发射极截止电流 Collector-emitter cut-off current	$V_{CE} = 1200\text{ V}, V_{GE} = 0\text{ V}, T_{vj} = 25^{\circ}\text{C}$		I_{CES}			5,0	mA
栅极-发射极漏电流 Gate-emitter leakage current	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}, T_{vj} = 25^{\circ}\text{C}$		I_{GES}			400	nA
开通延迟时间(电感负载) Turn-on delay time, inductive load	$I_C = 900\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 1,5\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_{don}	0,24 0,25 0,26			μs μs μs
上升时间(电感负载) Rise time, inductive load	$I_C = 900\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 1,5\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_r	0,09 0,10 0,11			μs μs μs
关断延迟时间(电感负载) Turn-off delay time, inductive load	$I_C = 900\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 0,9\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_{doff}	0,61 0,64 0,66			μs μs μs
下降时间(电感负载) Fall time, inductive load	$I_C = 900\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 0,9\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_f	0,14 0,17 0,18			μs μs μs
开通损耗能量(每脉冲) Turn-on energy loss per pulse	$I_C = 900\text{ A}, V_{CE} = 600\text{ V}, L_S = 60\text{ nH}$ $V_{GE} = \pm 15\text{ V}, di/dt = 6000\text{ A}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $R_{Gon} = 1,5\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{on}	40,0 55,0 60,0			mJ mJ mJ
关断损耗能量(每脉冲) Turn-off energy loss per pulse	$I_C = 900\text{ A}, V_{CE} = 600\text{ V}, L_S = 60\text{ nH}$ $V_{GE} = \pm 15\text{ V}, du/dt = 3000\text{ V}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $R_{Goff} = 0,9\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{off}	110 160 175			mJ mJ mJ
短路数据 SC data	$V_{GE} \leq 15\text{ V}, V_{CC} = 800\text{ V}$ $V_{CEmax} = V_{CES} - L_{SCE} \cdot di/dt$ $t_P \leq 10\ \mu\text{s}, T_{vj} = 150^{\circ}\text{C}$		I_{SC}	3600			A
结 - 外壳热阻 Thermal resistance, junction to case	每个 IGBT / per IGBT		R_{thJC}			0,0310	K/W
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个 IGBT / per IGBT $\lambda_{\text{Paste}} = 1\text{ W}/(\text{m}\cdot\text{K})$ / $\lambda_{\text{grease}} = 1\text{ W}/(\text{m}\cdot\text{K})$		R_{thCH}			0,0180	K/W
在开关状态下温度 Temperature under switching conditions			$T_{vj\text{op}}$	-40		150	$^{\circ}\text{C}$

二极管, 逆变器 / Diode, Inverter 最大额定值 / Maximum Rated Values

反向重复峰值电压 Repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{RRM}	1200	V
连续正向直流电流 Continuous DC forward current		I_F	900	A
正向重复峰值电流 Repetitive peak forward current	$t_P = 1\text{ ms}$	I_{FRM}	1800	A
I^2t -值 I^2t - value	$V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 125^{\circ}\text{C}$ $V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$	I^2t	91000 88000	A^2s A^2s

特征值 / Characteristic Values

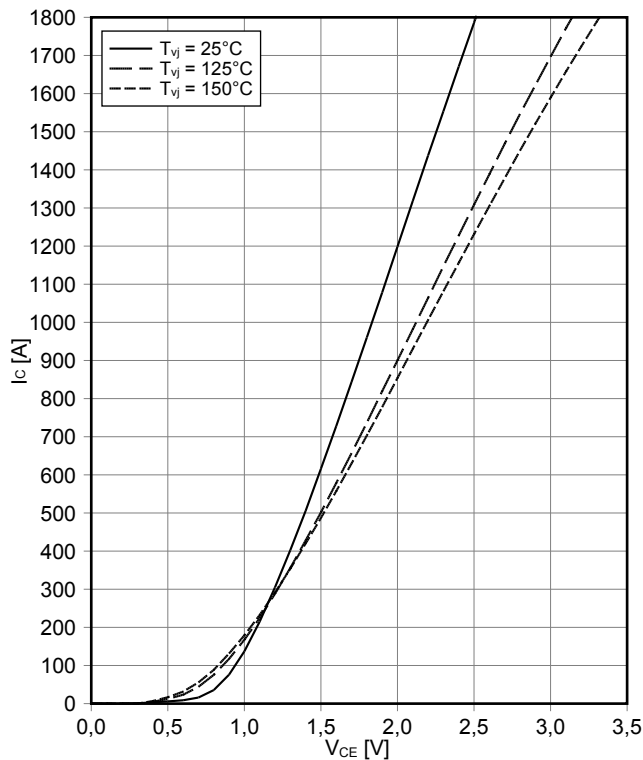
		min. typ. max.			
正向电压 Forward voltage	$I_F = 900\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 900\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 900\text{ A}, V_{GE} = 0\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	V_F	1,90 1,85 1,80	2,45 V V V
反向恢复峰值电流 Peak reverse recovery current	$I_F = 900\text{ A}, -di_F/dt = 6000\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 600\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	I_{RM}	540 720 750	A A A
恢复电荷 Recovered charge	$I_F = 900\text{ A}, -di_F/dt = 6000\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 600\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	Q_r	80,0 150 180	μC μC μC
反向恢复损耗 (每脉冲) Reverse recovery energy	$I_F = 900\text{ A}, -di_F/dt = 6000\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 600\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{rec}	40,0 75,0 85,0	mJ mJ mJ
结 - 外壳热阻 Thermal resistance, junction to case	每个二极管 / per diode		R_{thJC}		0,0560 K/W
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个二极管 / per diode $\lambda_{\text{Paste}} = 1\text{ W}/(\text{m}\cdot\text{K}) / \lambda_{\text{grease}} = 1\text{ W}/(\text{m}\cdot\text{K})$		R_{thCH}	0,0220	K/W
在开关状态下温度 Temperature under switching conditions			$T_{vj\text{ op}}$	-40	150 $^{\circ}\text{C}$

模块 / Module

绝缘测试电压 Isolation test voltage	RMS, $f = 50\text{ Hz}, t = 1\text{ min.}$	V_{ISOL}	4,0	kV
模块基板材料 Material of module baseplate			Cu	
内部绝缘 Internal isolation	基本绝缘 (class 1, IEC 61140) basic insulation (class 1, IEC 61140)		Al_2O_3	
爬电距离 Creepage distance	端子至散热器 / terminal to heatsink 端子至端子 / terminal to terminal		25,0 19,0	mm
电气间隙 Clearance	端子至散热器 / terminal to heatsink 端子至端子 / terminal to terminal		25,0 10,0	mm
相对电痕指数 Comperative tracking index		CTI	> 400	
		min. typ. max.		
杂散电感, 模块 Stray inductance module		L_{sCE}	16	nH
模块引线电阻, 端子-芯片 Module lead resistance, terminals - chip	$T_C = 25^{\circ}\text{C},$ 每个开关 / per switch	R_{CC+EE}	0,50	m Ω
储存温度 Storage temperature		T_{stg}	-40	125 $^{\circ}\text{C}$
模块安装的安装扭矩 Mounting torque for modul mounting	螺丝 M6 根据相应的应用手册进行安装 Screw M6 - Mounting according to valid application note	M	3,00	6,00 Nm
端子联接扭矩 Terminal connection torque	螺丝 M4 根据相应的应用手册进行安装 Screw M4 - Mounting according to valid application note 螺丝 M6 根据相应的应用手册进行安装 Screw M6 - Mounting according to valid application note	M	1,1 2,5	- - 2,0 5,0 Nm
重量 Weight		G	340	g

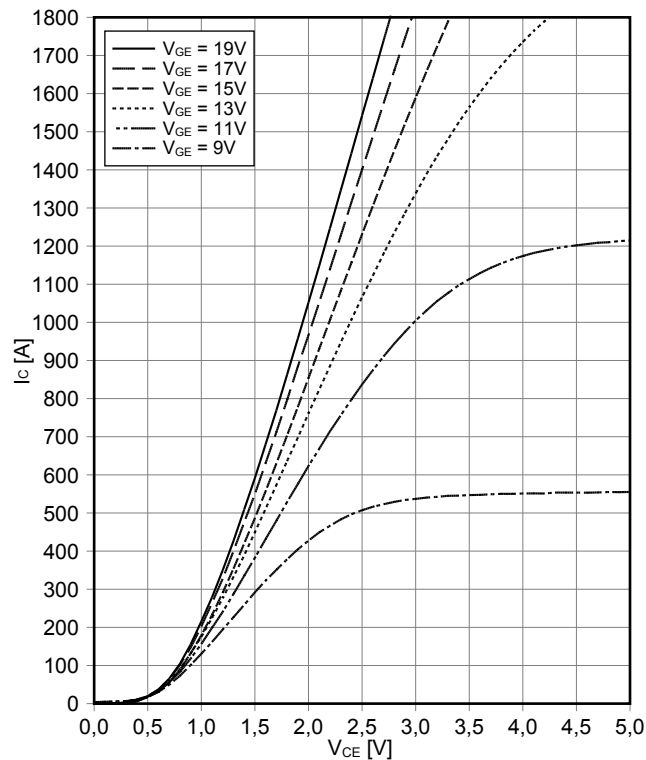
输出特性 IGBT, 逆变器 (典型)
output characteristic IGBT, Inverter (typical)

$I_C = f(V_{CE})$
 $V_{GE} = 15\text{ V}$



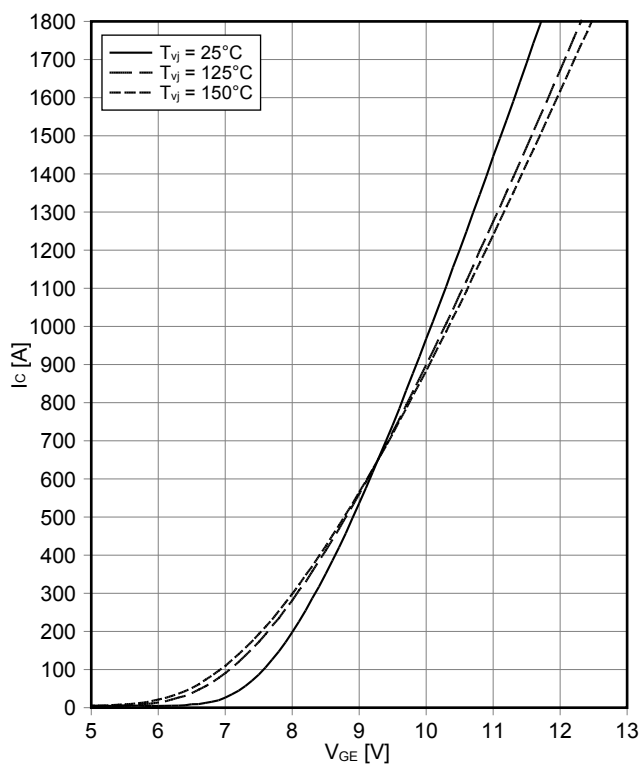
输出特性 IGBT, 逆变器 (典型)
output characteristic IGBT, Inverter (typical)

$I_C = f(V_{CE})$
 $T_{vj} = 150^\circ\text{C}$



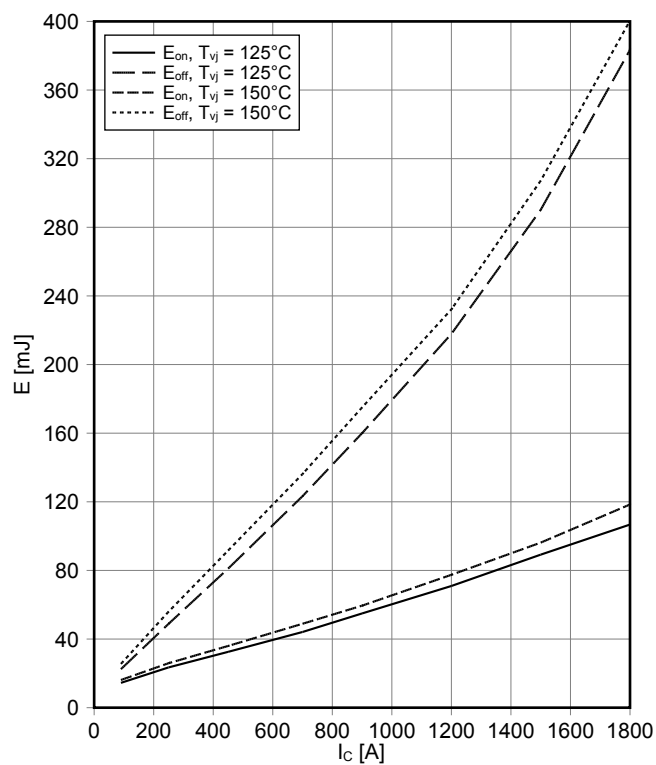
传输特性 IGBT, 逆变器 (典型)
transfer characteristic IGBT, Inverter (typical)

$I_C = f(V_{GE})$
 $V_{CE} = 20\text{ V}$



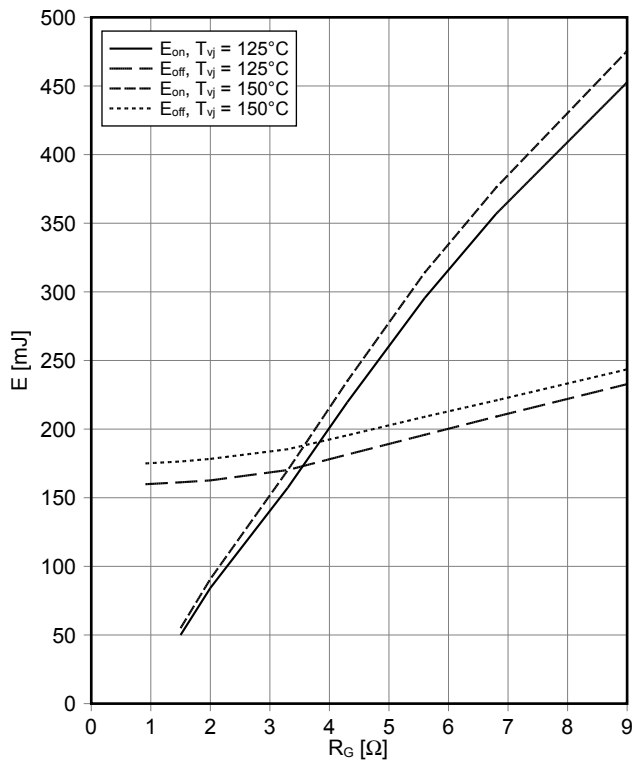
开关损耗 IGBT, 逆变器 (典型)
switching losses IGBT, Inverter (typical)

$E_{on} = f(I_C)$, $E_{off} = f(I_C)$
 $V_{GE} = \pm 15\text{ V}$, $R_{Gon} = 1.5\ \Omega$, $R_{Goff} = 0.9\ \Omega$, $V_{CE} = 600\text{ V}$

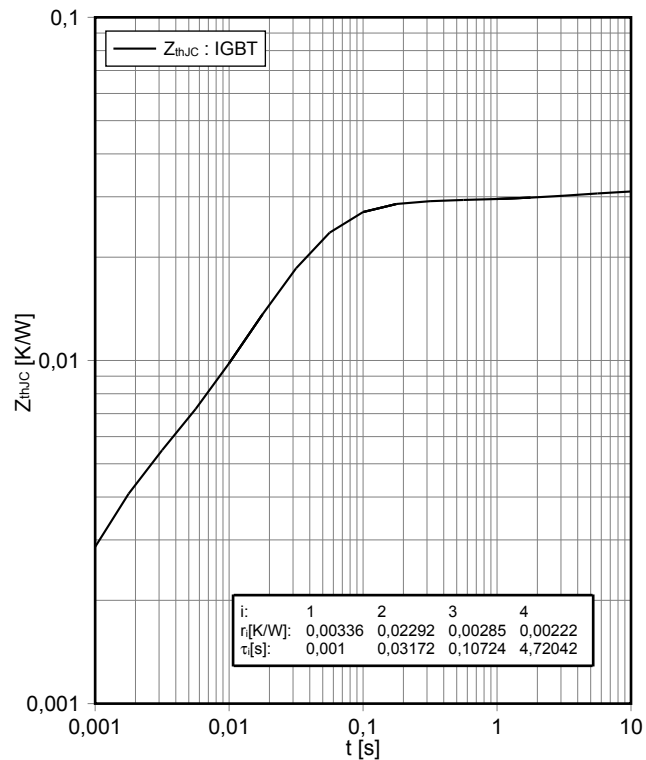


开关损耗 IGBT, 逆变器 (典型)
switching losses IGBT, Inverter (typical)

$E_{on} = f(R_G), E_{off} = f(R_G)$
 $V_{GE} = \pm 15 \text{ V}, I_C = 900 \text{ A}, V_{CE} = 600 \text{ V}$

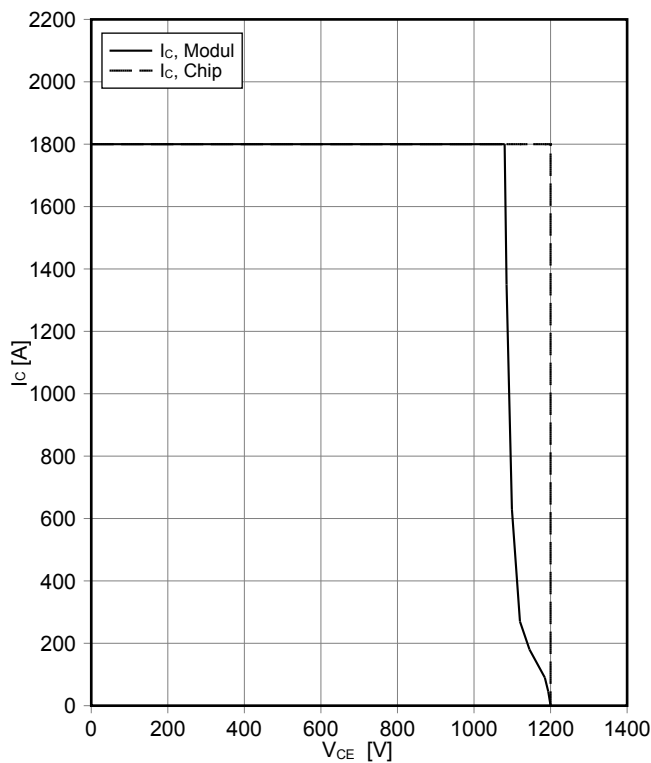


瞬态热阻抗 IGBT, 逆变器
transient thermal impedance IGBT, Inverter
 $Z_{thJC} = f(t)$

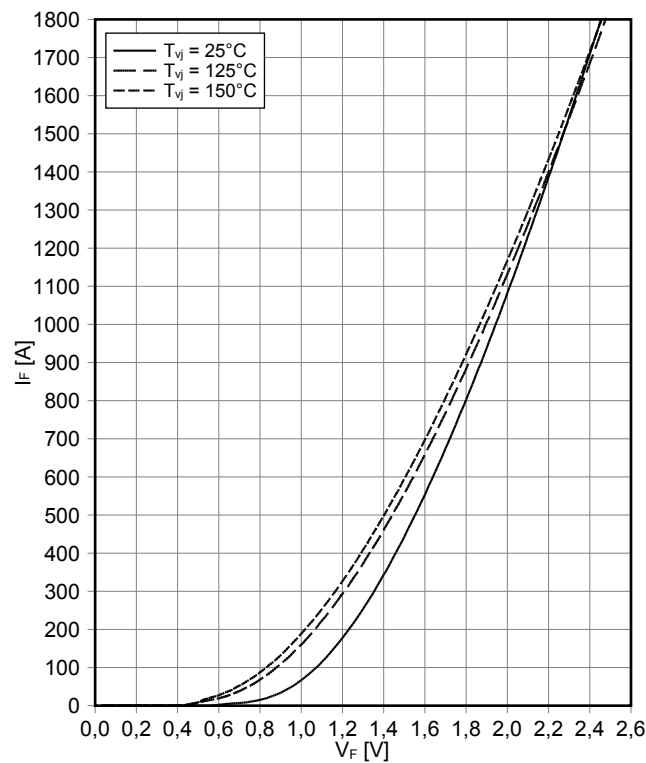


反偏安全工作区 IGBT, 逆变器 (RBSOA)
reverse bias safe operating area IGBT, Inverter (RBSOA)

$I_C = f(V_{CE})$
 $V_{GE} = \pm 15 \text{ V}, R_{Goff} = 0.9 \Omega, T_{vj} = 150^\circ\text{C}$

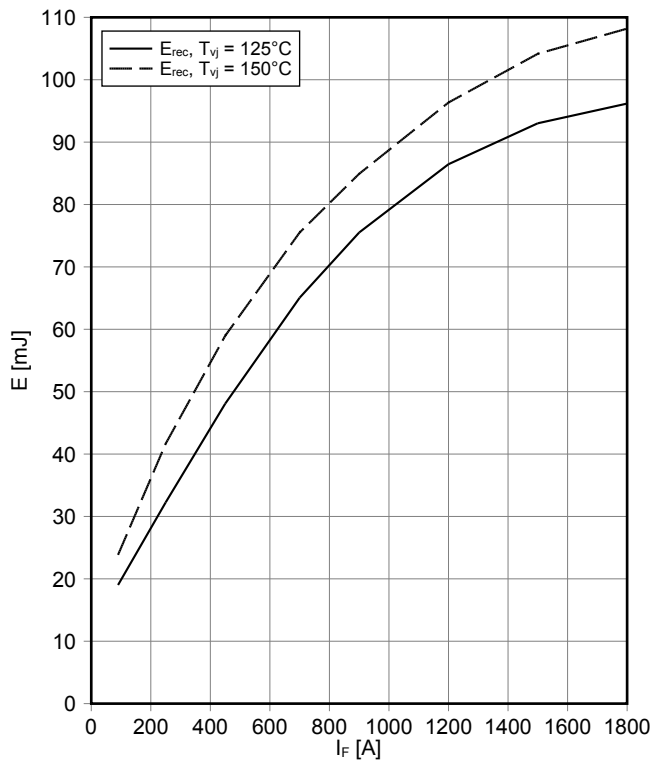


正向偏压特性 二极管, 逆变器 (典型)
forward characteristic of Diode, Inverter (typical)
 $I_F = f(V_F)$



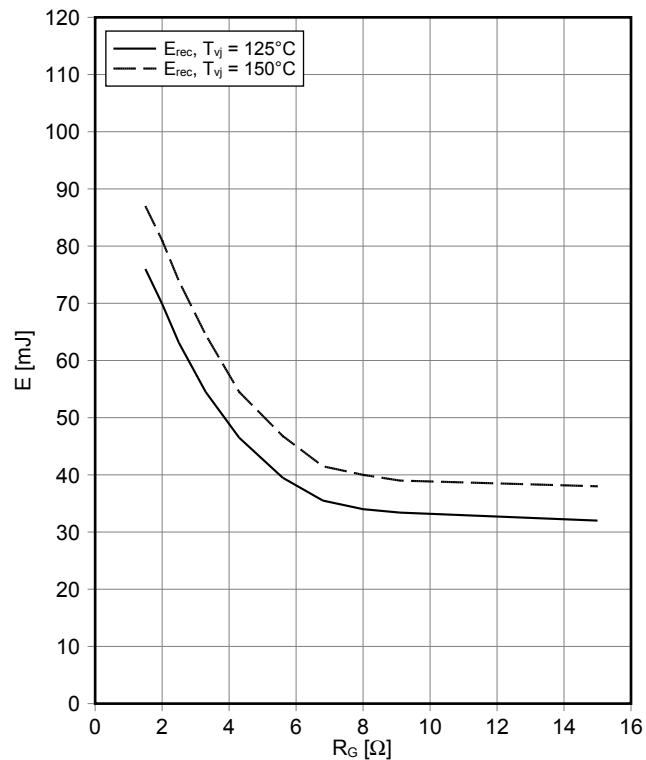
开关损耗 二极管,逆变器 (典型)
switching losses Diode, Inverter (typical)

$E_{rec} = f(I_F)$
 $R_{Gon} = 1.5 \Omega, V_{CE} = 600 V$



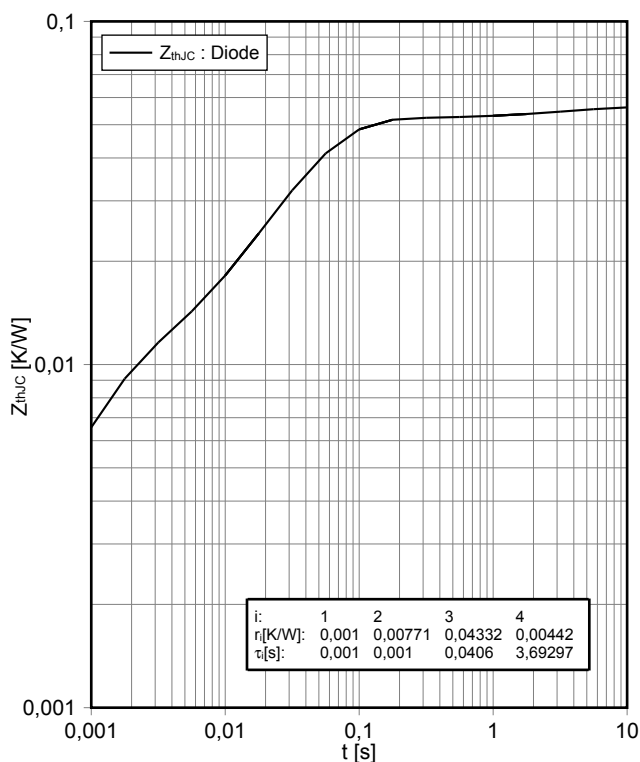
开关损耗 二极管,逆变器 (典型)
switching losses Diode, Inverter (typical)

$E_{rec} = f(R_G)$
 $I_F = 900 A, V_{CE} = 600 V$

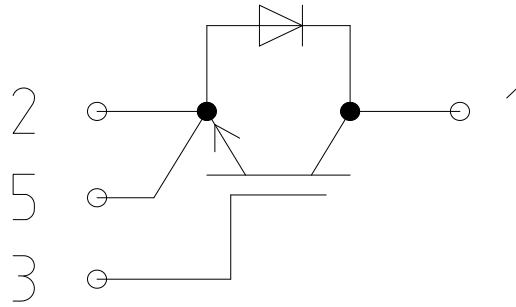


瞬态热阻抗 二极管,逆变器
transient thermal impedance Diode, Inverter

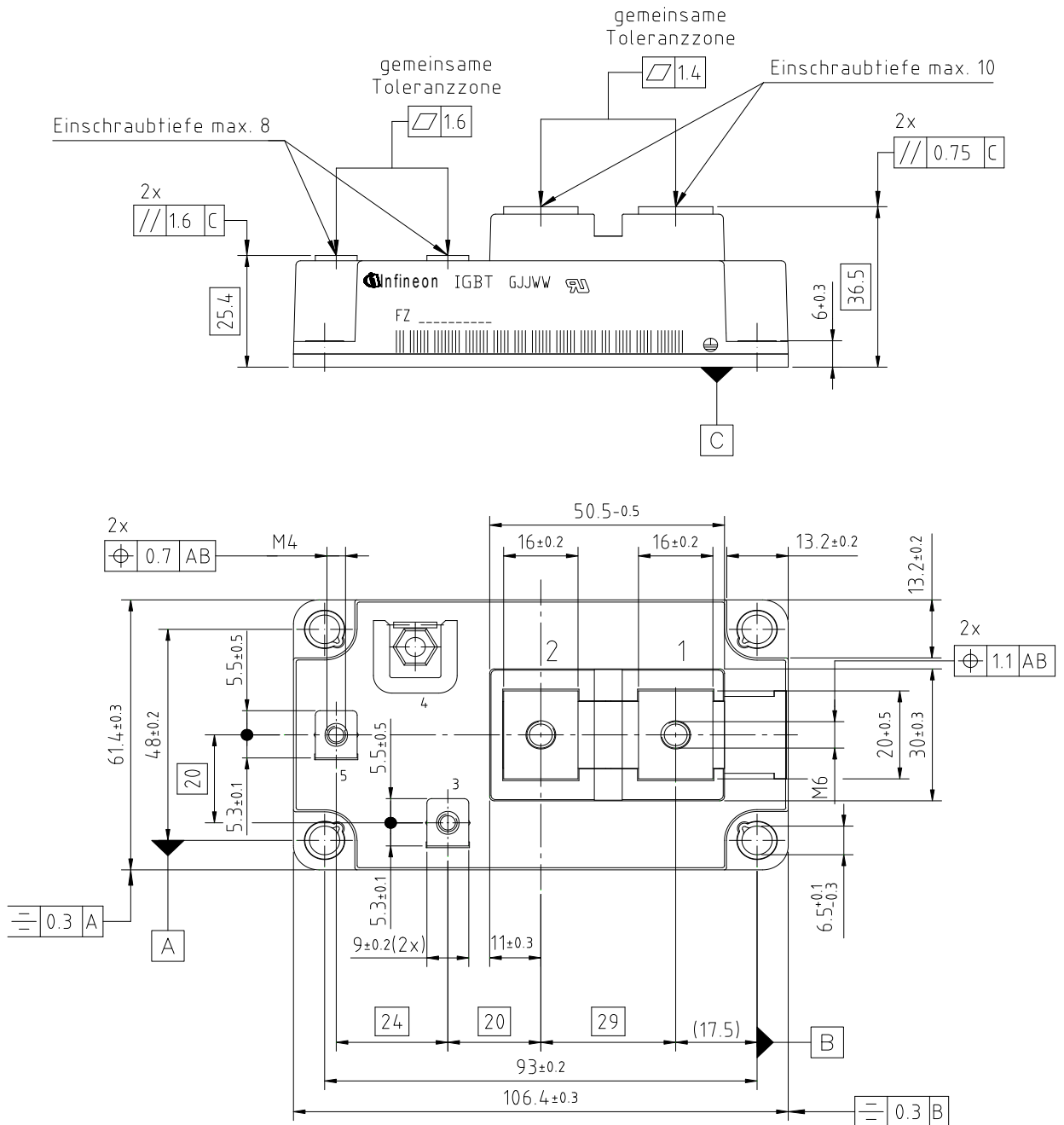
$Z_{thJC} = f(t)$



接线图 / Circuit diagram



封装尺寸 / Package outlines



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